



P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^b	
- 30	0.072 at V _{GS} = - 10 V	- 2.8	
	0.120 at V _{GS} = - 4.5 V	- 2.0	

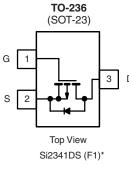
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETS
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- · Load Switch
- PA Switch



* Marking Code

Ordering Information: Si2341DS-T1-E3 (Lead (Pb)-free)

Si2341DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		V	
Gate-Source Voltage		V_{GS}	± 20			
Continuous Drain Current (T _{.I} = 150 °C) ^b	T _A = 25 °C	- I _D	- 2.8	- 2.5	Α	
Continuous Diain Curient (1) = 130°C)	T _A = 70 °C		- 2.2	- 2.0		
Pulsed Drain Current ^a		I _{DM}	- 12			
Continuous Source Current (Diode Conduction) ^b		I _S	- 0.75	- 0.6		
Power Dissipation ^b	T _A = 25 °C	- P _D	0.9	0.71	W	
rowei Dissipation	T _A = 70 °C		0.57	0.45		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	В	115	140	°C/W
Maximum Junction-to-Ambient ^c	- R _{thJA}	140	175	
Maximum Junction-to-Foot (Drain)	R _{thJF}	60	75	

Notes:

- a. Pulse width limited by maximum junction temperature.
- b. Surface mounted on FR4 board, $t \le 5$ s.
- c. Surface mounted on FR4 board.

Si2341DS

Vishay Siliconix



MOSFET SPECIFICATIO	N5 $I_J = 25$	C, unless otherwise noted					
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	1			T	I	ı	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_{D} = -10 \mu\text{A}$	- 30			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.0		- 3.0	•	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = - 24 V, V _{GS} = 0 V			- 1	- μΑ	
	I _{DSS}	V _{DS} = - 24 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, $V_{GS} =$ - 10 V	- 6			Α	
Drain Course On Registeness	В	V _{GS} = - 10 V, I _D = - 2.8 A		0.057	0.072	Ω	
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2.0 A		0.090	0.120		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 2.8 A		8.0		S	
Diode Forward Voltage	V _{SD}	I _S = - 0.75 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			9.5	15		
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}$ $I_{D} \cong -2.8 \text{ A}$		1.5		nC	
Gate-Drain Charge	Q _{gd}	D = 2.0 · ·		2.5			
Input Capacitance	C _{iss}			400			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		95		pF	
Reverse Transfer Capacitance	C _{rss}			70			
Switching ^c							
Turn On Time	t _{d(on)}	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$		7	15	-	
Turn-On Time	t _r			15	25		
Turn Off Time	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V R_α = 6 Ω		20	30	ns	
Turn-Off Time	t _f	j		20	30]	

Notes:

- a. Pulse test: PW \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

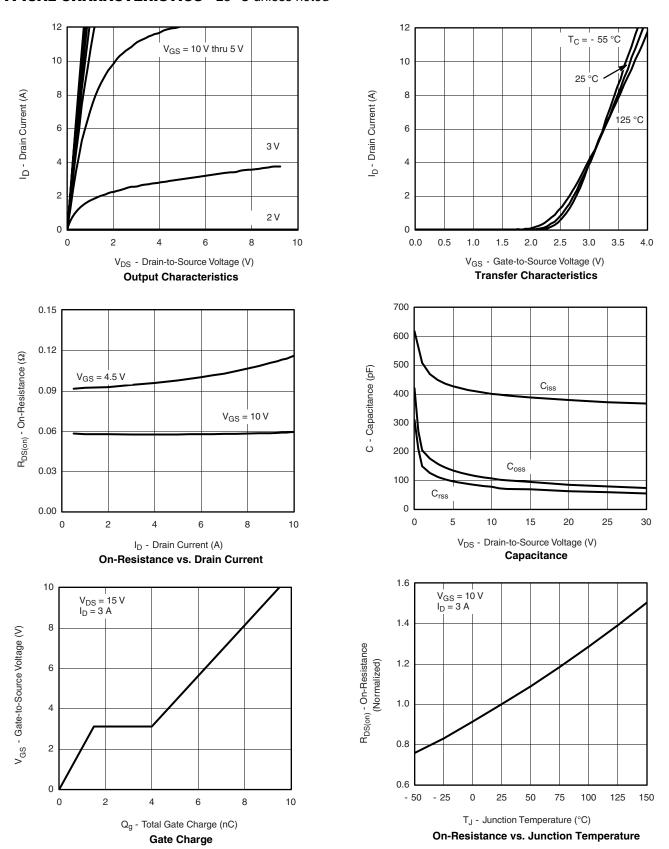
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.







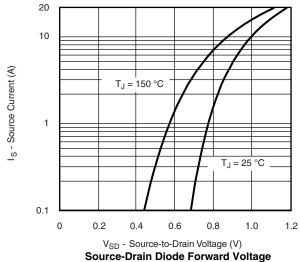
TYPICAL CHARACTERISTICS 25 °C unless noted

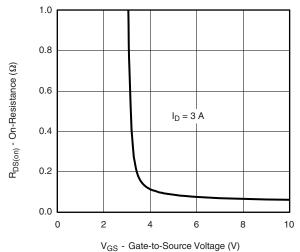


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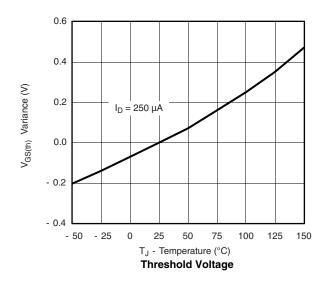
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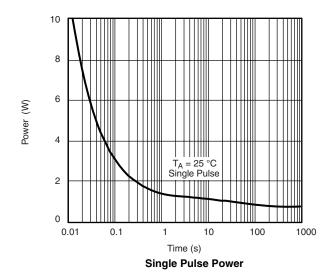
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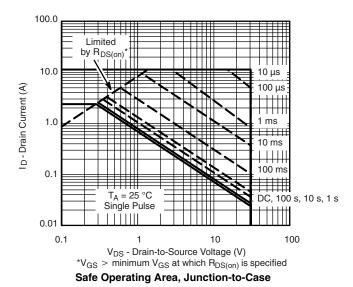




ode Forward Voltage
On-Resistance vs. Gate-to-Source Voltage

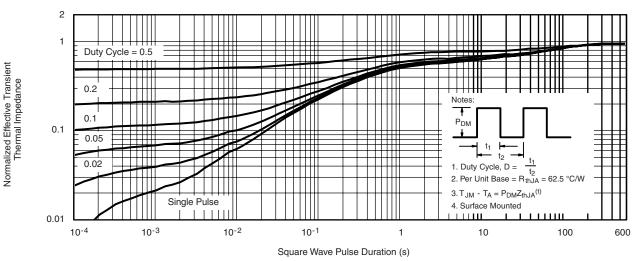








TYPICAL CHARACTERISTICS 25 °C unless noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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